

HEXFET® Power MOSFET

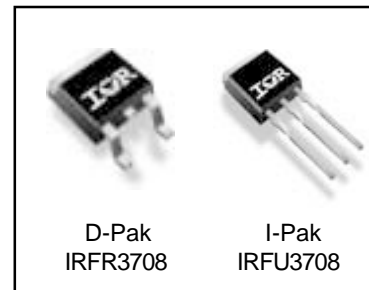
**Applications**

- High Frequency DC-DC Isolated Converters with Synchronous Rectification for Telecom and Industrial Use
- High Frequency Buck Converters for Computer Processor Power

$V_{DSS}$	$R_{DS(on)}$ max	$I_D$
30V	12.5m $\Omega$	61A <sup>④</sup>

**Benefits**

- Ultra-Low Gate Impedance
- Very Low  $R_{DS(on)}$  at 4.5V  $V_{GS}$
- Fully Characterized Avalanche Voltage and Current



**Absolute Maximum Ratings**

Symbol	Parameter	Max.	Units
$V_{DS}$	Drain-Source Voltage	30	V
$V_{GS}$	Gate-to-Source Voltage	$\pm 12$	V
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	61 <sup>④</sup>	A
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	51 <sup>④</sup>	
$I_{DM}$	Pulsed Drain Current <sup>①</sup>	244	
$P_D @ T_A = 25^\circ\text{C}$	Maximum Power Dissipation <sup>③</sup>	87	W
$P_D @ T_A = 70^\circ\text{C}$	Maximum Power Dissipation <sup>③</sup>	61	W
	Linear Derating Factor	0.58	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 175	$^\circ\text{C}$

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.73	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	—	50	
$R_{\theta JA}$	Junction-to-Ambient	—	110	

\* When mounted on 1" square PCB (FR-4 or G-10 Material) .  
For recommended footprint and soldering techniques refer to application note #AN-994

Notes ① through ④ are on page 9

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## Static @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	30	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.028	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	8.5	12.5	m $\Omega$	$V_{GS} = 10V, I_D = 15A$ ③
		—	10.0	14.0		$V_{GS} = 4.5V, I_D = 12A$ ③
		—	15.0	30.0		$V_{GS} = 2.8V, I_D = 7.5A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	0.6	—	2.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	20	$\mu A$	$V_{DS} = 24V, V_{GS} = 0V$
		—	—	100		$V_{DS} = 24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	200	nA	$V_{GS} = 12V$
	Gate-to-Source Reverse Leakage	—	—	-200		$V_{GS} = -12V$

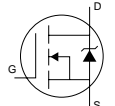
## Dynamic @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$g_{fs}$	Forward Transconductance	49	—	—	S	$V_{DS} = 15V, I_D = 50A$
$Q_g$	Total Gate Charge	—	24	—	nC	$I_D = 24.8A$ $V_{DS} = 15V$ $V_{GS} = 4.5V$ ③
$Q_{gs}$	Gate-to-Source Charge	—	6.7	—		
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	5.8	—		
$Q_{oss}$	Output Gate Charge	—	14	21		
$t_{d(on)}$	Turn-On Delay Time	—	7.2	—	ns	$V_{DD} = 15V$ $I_D = 24.8A$ $R_G = 0.6\Omega$ $V_{GS} = 4.5V$ ③
$t_r$	Rise Time	—	50	—		
$t_{d(off)}$	Turn-Off Delay Time	—	17.6	—		
$t_f$	Fall Time	—	3.7	—		
$C_{iss}$	Input Capacitance	—	2417	—	pF	$V_{GS} = 0V$ $V_{DS} = 15V$ $f = 1.0\text{MHz}$
$C_{oss}$	Output Capacitance	—	707	—		
$C_{rss}$	Reverse Transfer Capacitance	—	52	—		

## Avalanche Characteristics

Symbol	Parameter	Typ.	Max.	Units
$E_{AS}$	Single Pulse Avalanche Energy②	—	213	mJ
$I_{AR}$	Avalanche Current①	—	62	A

## Diode Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	61④	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	244		
$V_{SD}$	Diode Forward Voltage	—	0.88	1.3	V	$T_J = 25^\circ\text{C}, I_S = 31A, V_{GS} = 0V$ ③
		—	0.80	—		$T_J = 125^\circ\text{C}, I_S = 31A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	41	62	ns	$T_J = 25^\circ\text{C}, I_F = 31A, V_R = 20V$
$Q_{rr}$	Reverse Recovery Charge	—	64	96	nC	$di/dt = 100A/\mu s$ ③
$t_{rr}$	Reverse Recovery Time	—	43	65	ns	$T_J = 125^\circ\text{C}, I_F = 31A, V_R = 20V$
$Q_{rr}$	Reverse Recovery Charge	—	70	105	nC	$di/dt = 100A/\mu s$ ③

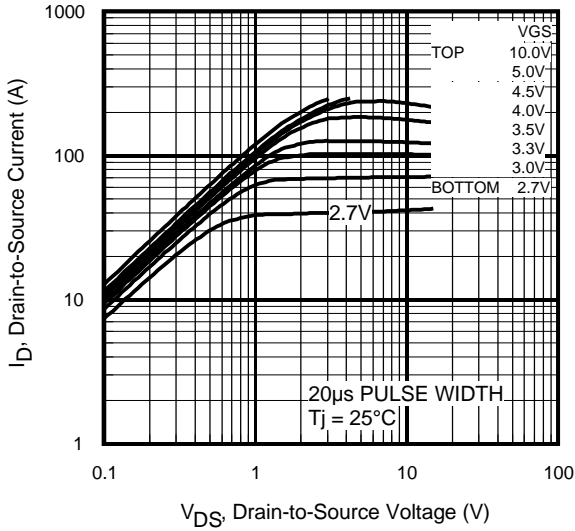


Fig 1. Typical Output Characteristics

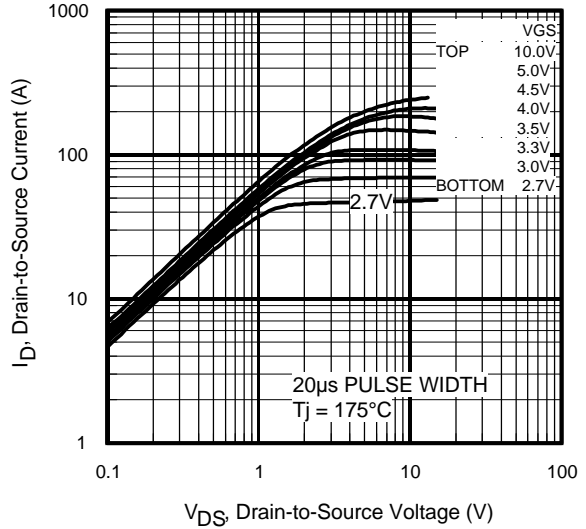


Fig 2. Typical Output Characteristics

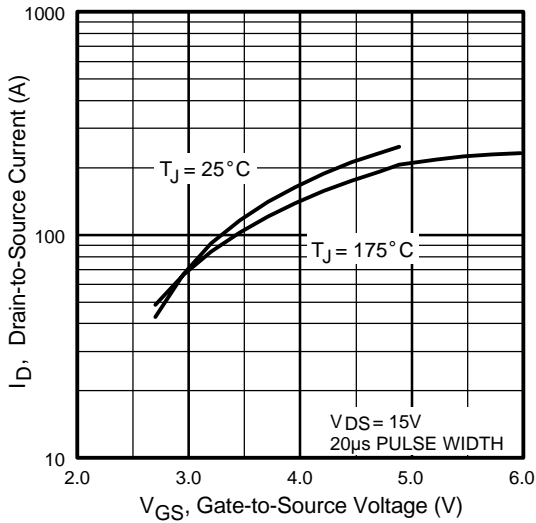


Fig 3. Typical Transfer Characteristics

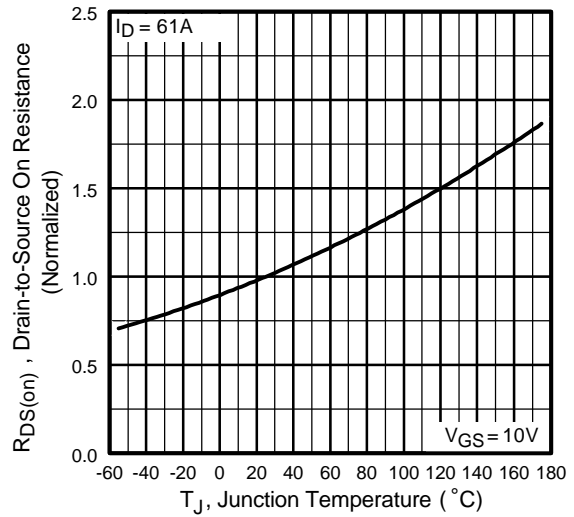
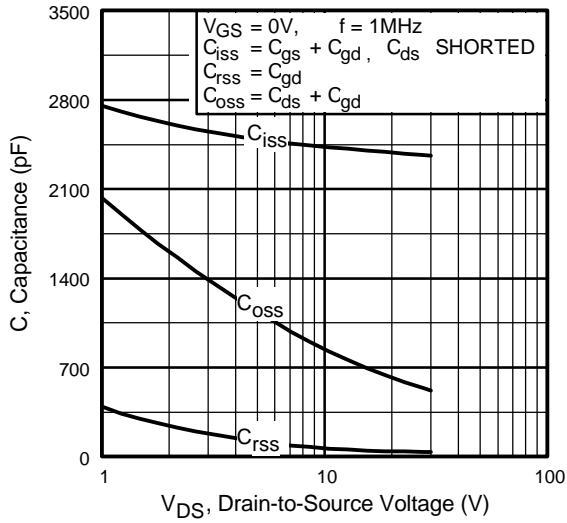
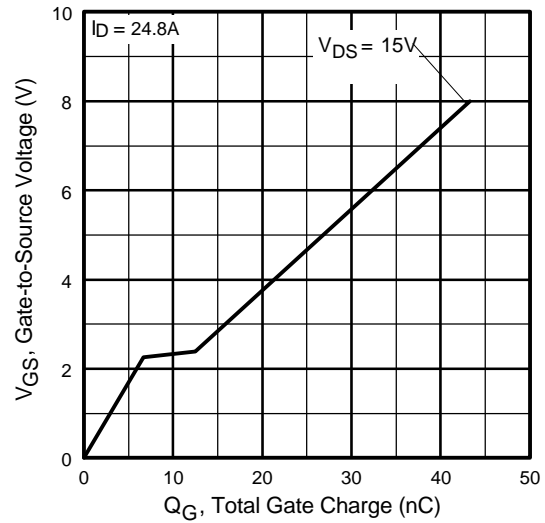


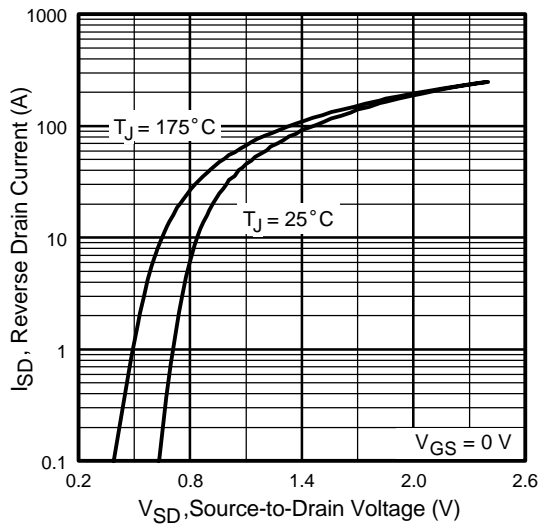
Fig 4. Normalized On-Resistance Vs. Temperature



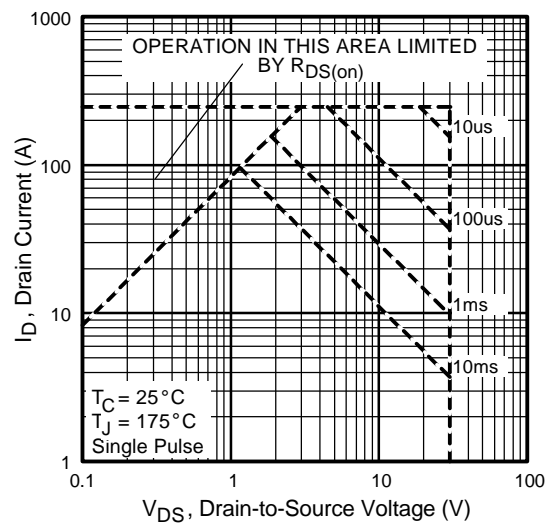
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



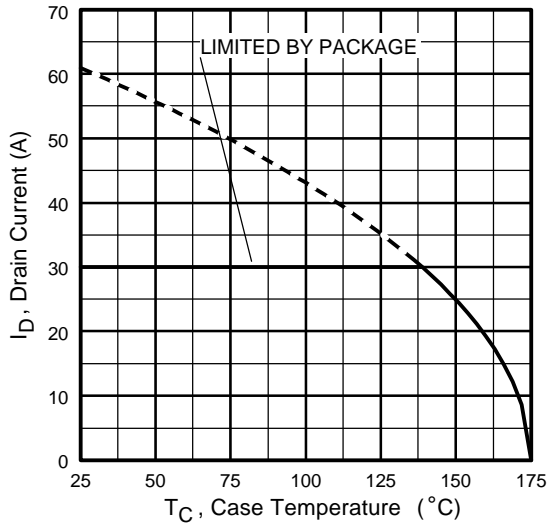
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



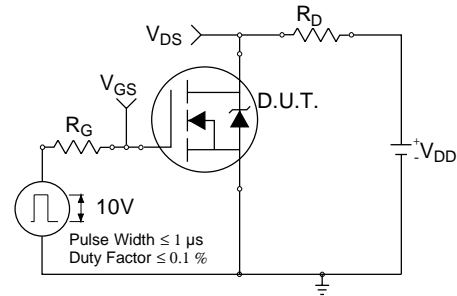
**Fig 7.** Typical Source-Drain Diode Forward Voltage



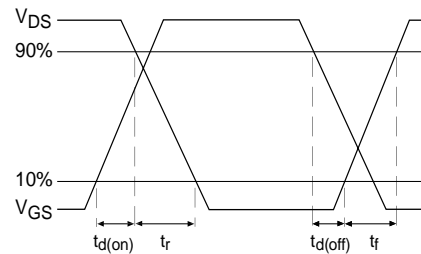
**Fig 8.** Maximum Safe Operating Area



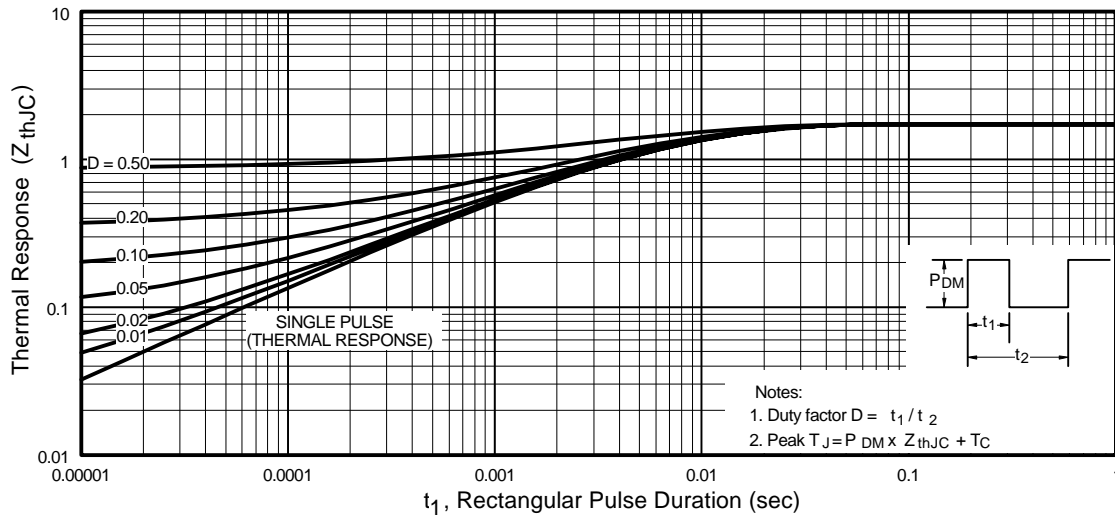
**Fig 9.** Maximum Drain Current Vs. Case Temperature



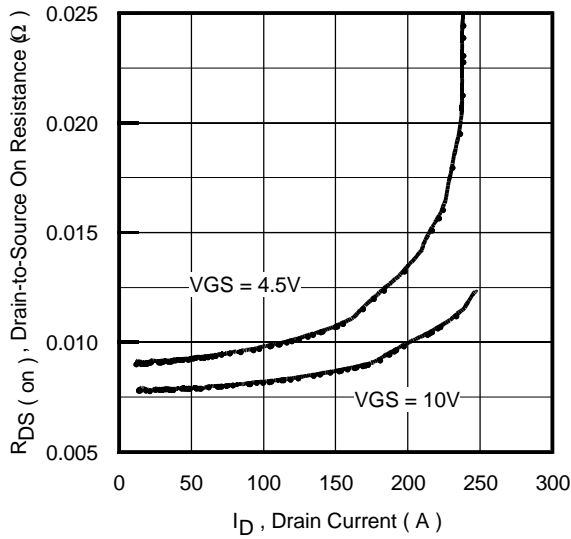
**Fig 10a.** Switching Time Test Circuit



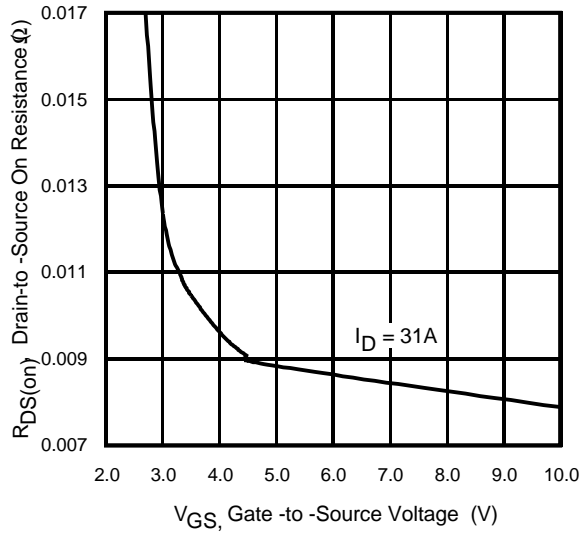
**Fig 10b.** Switching Time Waveforms



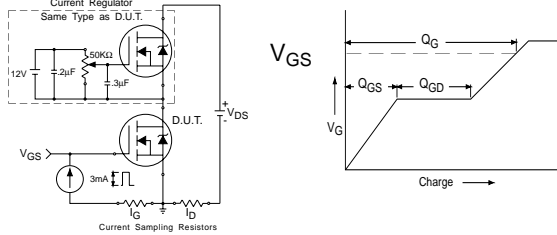
**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case



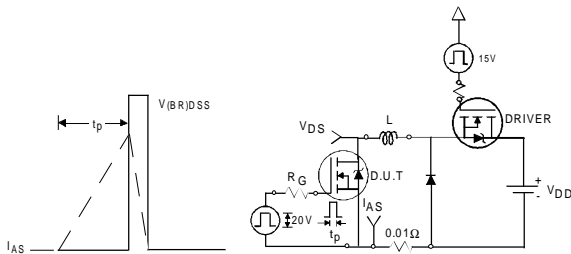
**Fig 12.** On-Resistance Vs. Drain Current



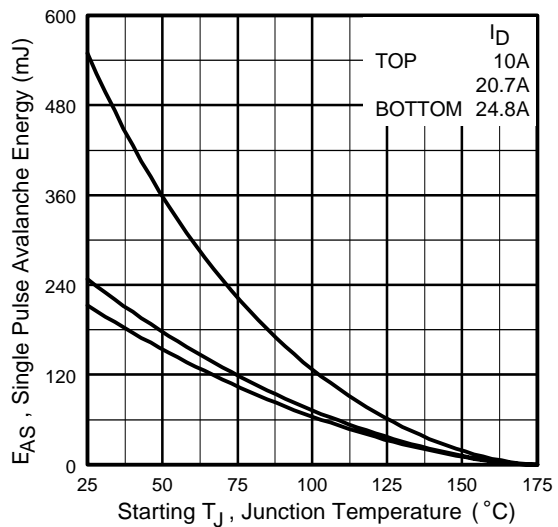
**Fig 13.** On-Resistance Vs. Gate Voltage



**Fig 14a&b.** Gate Charge Test Circuit and Waveform



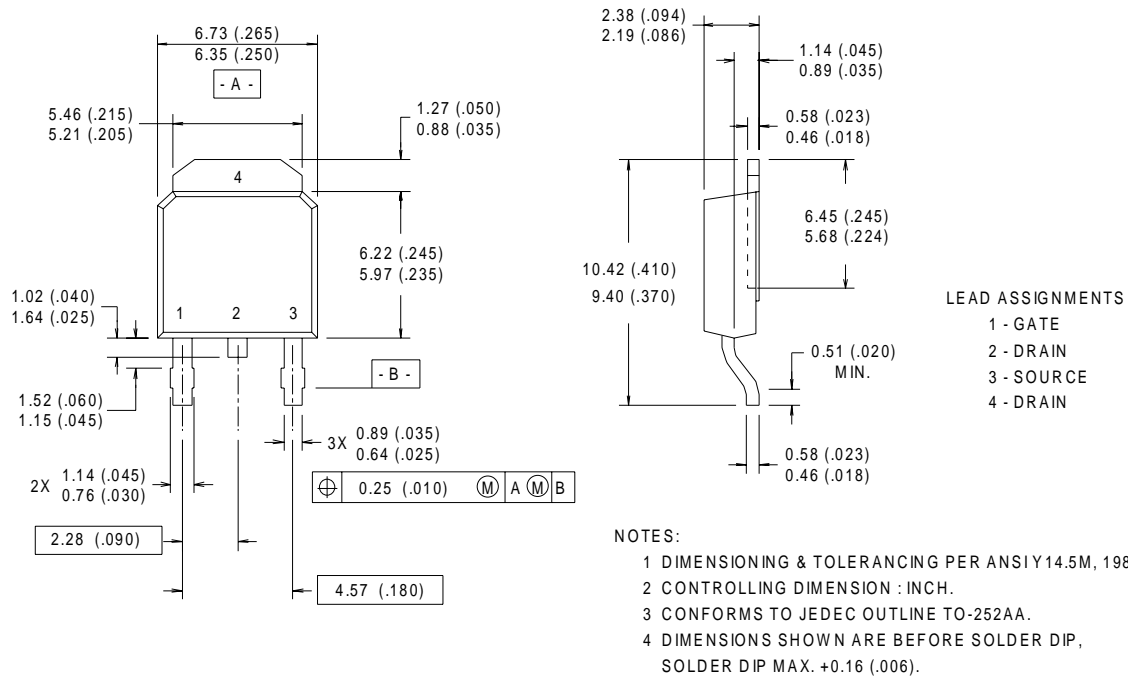
**Fig 15a&b.** Unclamped Inductive Test circuit and Waveforms



**Fig 15c.** Maximum Avalanche Energy Vs. Drain Current

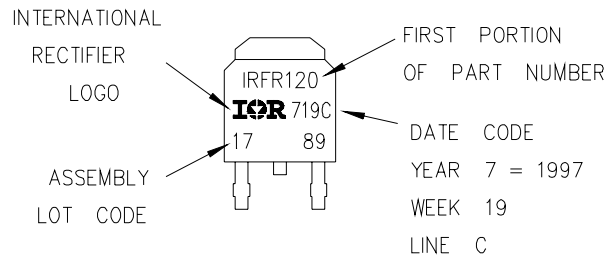
## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



## D-Pak (TO-252AA) Part Marking Information

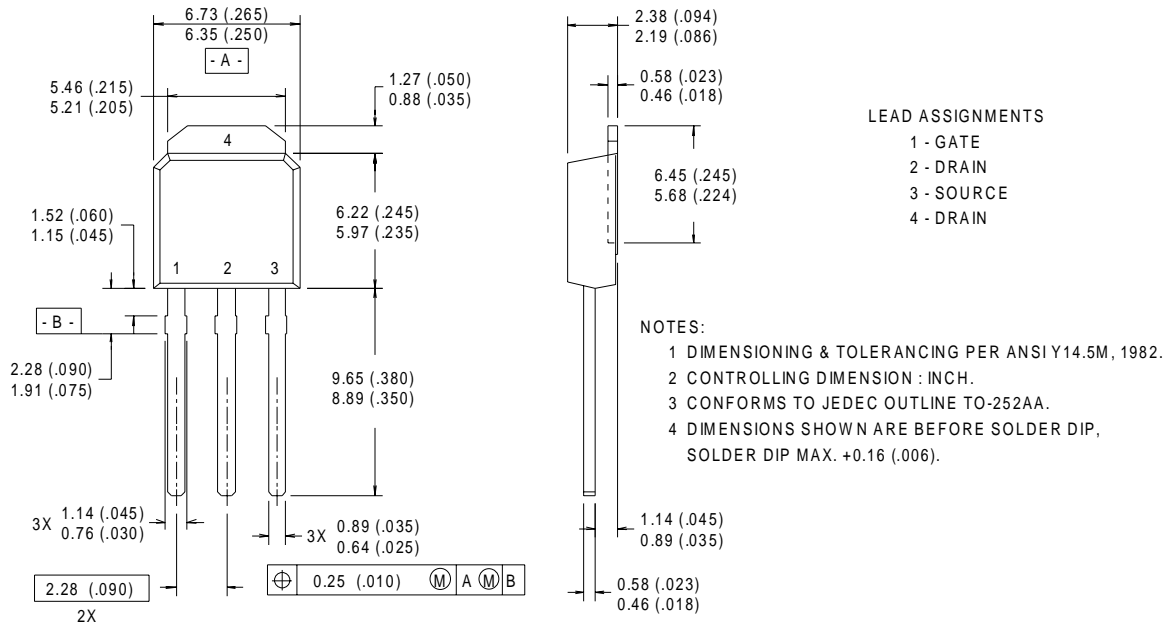
EXAMPLE: THIS IS AN IRFR120  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"



# IRFR/U3708

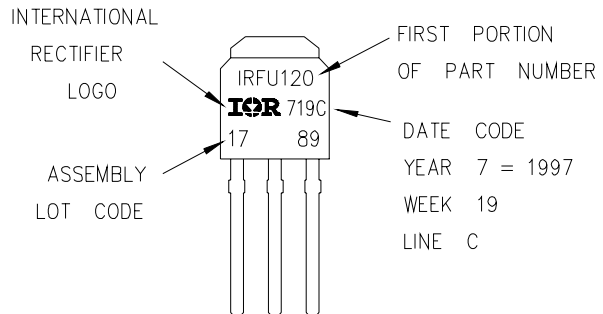
## I-Pak (TO-251AA) Package Outline

Dimensions are shown in millimeters (inches)



## I-Pak (TO-251AA) Part Marking Information

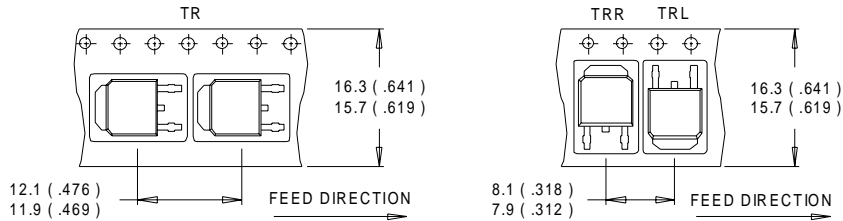
EXAMPLE: THIS IS AN IRFU120  
 LOT CODE 1789  
 ASSEMBLED ON WW 19, 1997  
 IN THE ASSEMBLY LINE "C"



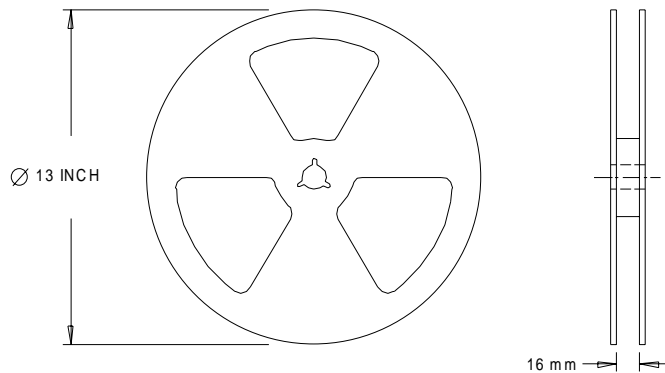


**D-Pak (TO-252AA) Tape & Reel Information**

Dimensions are shown in millimeters (inches)



- NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
  2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
  3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES :
1. OUTLINE CONFORMS TO EIA-481.

**Notes:**

- ① Repetitive rating; pulse width limited by max. junction temperature.
- ② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 0.7 \text{ mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = 24.8 \text{ A}$ .
- ③ Pulse width  $\leq 300\mu\text{s}$ ; duty cycle  $\leq 2\%$ .
- ④ Calculated continuous current based on maximum allowable junction temperature. Package limitation current is 30A.